

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	234mΩ @ 10V	2A
	267mΩ @ 6V	
	278mΩ @ 4.5V	

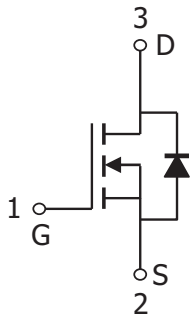
Features

- TrenchFET Power MOSFET
- Low $R_{DS(ON)}$.
- Surface mount package.

Mechanical data

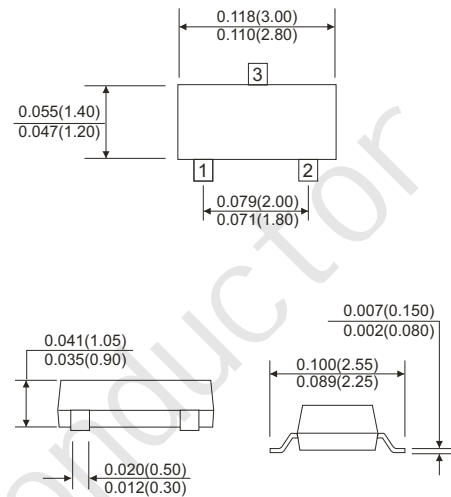
- Case: SOT-23, molded plastic.

Circuit diagram



1. GATE
2. SOURCE
3. DRAIN

SOT-23



Dimensions in inches and (millimeter)

Absolute Maximum Ratings (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	±20	V
Continuous drain current	I_D	2	A
Pulsed drain current	I_{DM}^*	8	A
Power dissipation	P_D	350	mW
Thermal resistance from junction to ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction temperature	T_J	-40 to +150	$^\circ\text{C}$
Storage temperature	T_{STG}	-55 to +150	$^\circ\text{C}$
Lead temperature for soldering purposes(1/8" form case for 10 s)	T_L	260	$^\circ\text{C}$

* Repetitive rating; Pulse width limited by junction temperature.

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage (note 1)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2		2.8	V
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.5A$			234	m Ω
		$V_{GS} = 6V, I_D = 1A$			267	
		$V_{GS} = 4.5V, I_D = 0.5A$			278	
Forward transconductance (note 1)	g_{FS}	$V_{DS} = 20V, I_D = 1.5A$		2		S
Diode forward voltage (note 1)	V_{SD}	$I_S = 1.3A, V_{GS} = 0V$			1.2	V
DYNAMIC PARAMETERS (note2)						
Input capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		190		pF
Output capacitance	C_{oss}			22		
Reverse transfer capacitance	C_{rss}			13		
Gate resistance	R_g	$F=1MHz$	0.3		2.8	Ω
SWITCHING PARAMETERS (note2)						
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50V, V_{GEN}=4.5V$ $R_L=39\Omega, R_G=1\Omega, I_D=1.3A$			45	nS
Turn-on rise time	t_r				39	
Turn-off delay time	$t_{d(off)}$				26	
Turn-on fall time	t_f				20	
Total gate charge	Q_g	$V_{DS}=50V, V_{GS}=4.5V$ $I_D=1.6A$			5.8	nC
Gate-source charge	Q_{gs}			0.75		
Gate-drain charge	Q_{gd}			1.4		

Note:

1. Pulse test : Pulse width $\leq 300\mu s$, duty cycle $\leq 0.5\%$.
2. Guaranteed by design, not subject to production testing.

Fig.1 - Output Characteristics

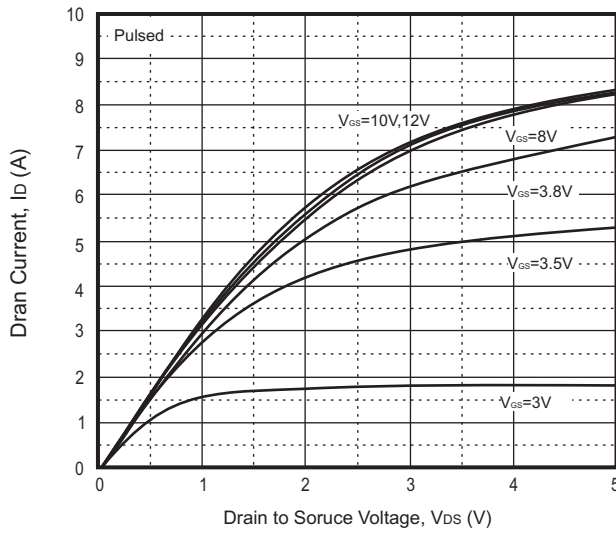


Fig.2 - Transfer Characteristics

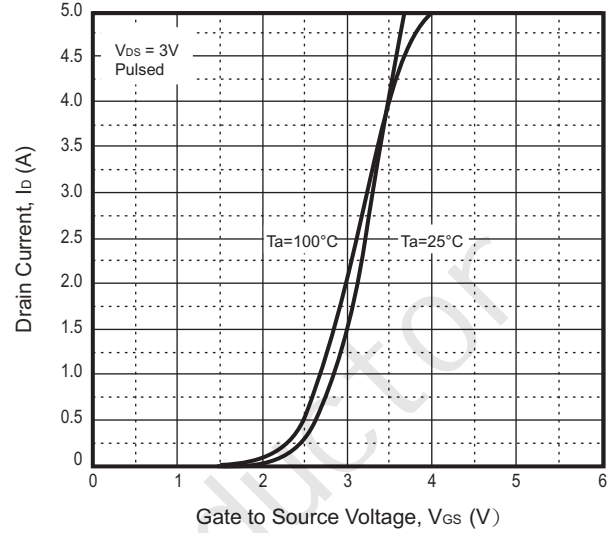
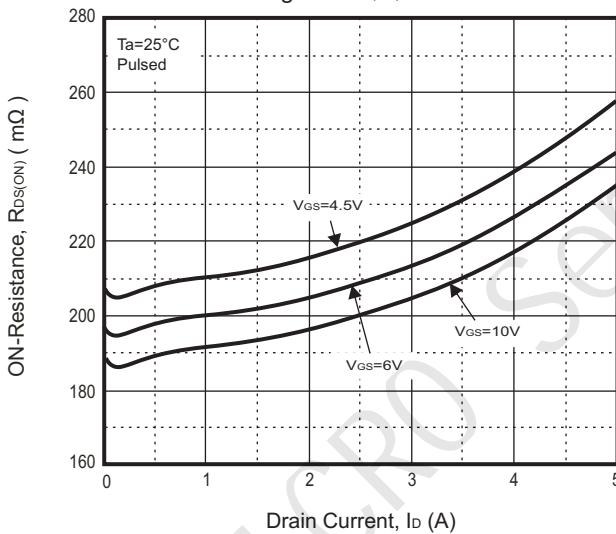
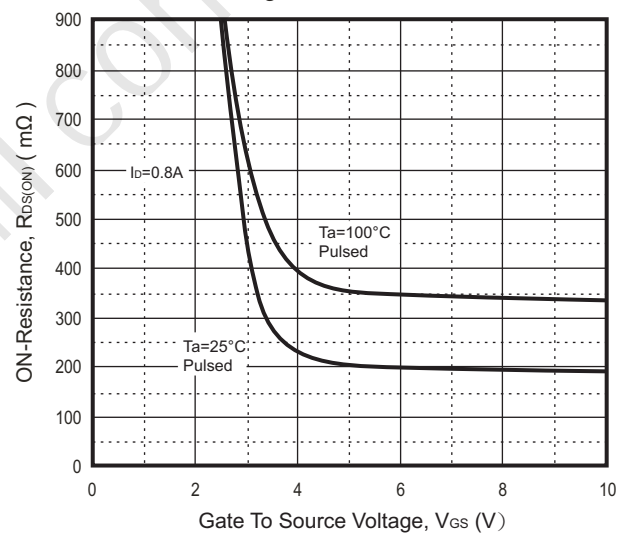
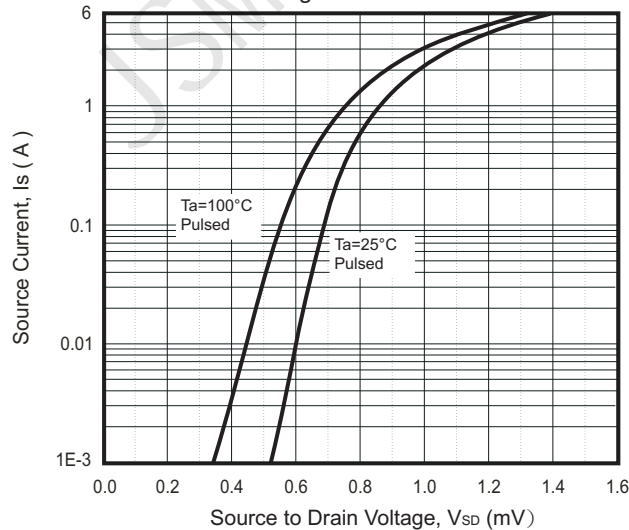

 Fig.3 - $R_{DS(ON)} - I_D$

 Fig.4 - $R_{DS(ON)} - V_{GS}$

 Fig.5 - $I_S - V_{SD}$


Fig.6 - Threshold Voltage

